



General Description

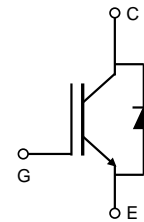
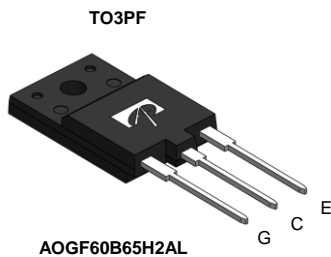
- Latest AlphaGBT (αIGBT) Technology
- 650V breakdown voltage
- Very fast and soft recovery freewheeling diode
- High efficient turn-on di/dt controllability
- Very high switching speed
- Low turn-off switching loss and softness
- Very good EMI behavior

Applications

- Power factor correction
- Very high switching frequency applications

Product Summary

V_{CE}	650V
I_C ($T_C=100^\circ\text{C}$)	60A
$V_{CE(sat)}$ ($T_J=25^\circ\text{C}$)	1.95V



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOGF60B65H2AL	TO3PF	Tube	480

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	AOGF60B65H2AL	Units
Collector-Emitter Voltage	V_{CE}	650	V
Gate-Emitter Voltage	V_{GE}	± 30	V
Continuous Collector Current	I_C	$T_C=25^\circ\text{C}$	120 ⁽²⁾
		$T_C=100^\circ\text{C}$	60 ⁽²⁾
Pulsed Collector Current, Limited by T_{Jmax}	I_{CM}	180	A
Turn-Off SOA, $V_{CE} \leq 650\text{V}$, Limited by T_{Jmax}	I_{LM}	180	A
Continuous Diode Forward Current	I_F	$T_C=25^\circ\text{C}$	60 ⁽²⁾
		$T_C=100^\circ\text{C}$	30 ⁽²⁾
Diode Pulsed Current, Limited by T_{Jmax}	I_{FM}	90	A
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	74
		$T_C=100^\circ\text{C}$	29
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	AOGF60B65H2AL	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	30	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	1.7	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$

(1) TO3PF I_C, I_F follows TO247.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV _{CES}	Collector-Emitter Breakdown Voltage	I _C =1mA, V _{GE} =0V, T _J =25°C	650	-	-	V	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V, I _C =60A	T _J =25°C	-	1.95	2.5	V
			T _J =125°C	-	2.45	-	
			T _J =150°C	-	2.58	-	
V _F	Diode Forward Voltage	V _{GE} =0V, I _F =30A	T _J =25°C	-	1.88	2.4	V
			T _J =125°C	-	1.97	-	
			T _J =150°C	-	1.94	-	
V _{GE(th)}	Gate-Emitter Threshold Voltage	V _{CE} =5V, I _C =1mA	-	4.6	-	V	
I _{CES}	Zero Gate Voltage Collector Current	V _{CE} =650V, V _{GE} =0V	T _J =25°C	-	-	10	μA
			T _J =125°C	-	-	1000	
			T _J =150°C	-	-	5000	
I _{GES}	Gate-Emitter Leakage Current	V _{CE} =0V, V _{GE} =±30V	-	-	±100	nA	
g _{FS}	Forward Transconductance	V _{CE} =20V, I _C =60A	-	33	-	S	
DYNAMIC PARAMETERS							
C _{ies}	Input Capacitance	V _{GE} =0V, V _{CC} =25V, f=1MHz	-	2100	-	pF	
C _{oes}	Output Capacitance		-	185	-	pF	
C _{res}	Reverse Transfer Capacitance		-	65	-	pF	
Q _g	Total Gate Charge	V _{GE} =15V, V _{CC} =520V, I _C =60A	-	84	-	nC	
Q _{ge}	Gate to Emitter Charge		-	21	-	nC	
Q _{gc}	Gate to Collector Charge		-	38	-	nC	
R _g	Gate Resistance	V _{GE} =0V, V _{CC} =0V, f=1MHz	-	15	-	Ω	
SWITCHING PARAMETERS, (Load Inductive, T_J=25°C)							
t _{D(on)}	Turn-On Delay Time	T _J =25°C V _{GE} =15V, V _{CC} =400V, I _C =60A, R _G =5Ω	-	35	-	ns	
t _r	Turn-On Rise Time		-	80	-	ns	
t _{D(off)}	Turn-Off Delay Time		-	168	-	ns	
t _f	Turn-Off Fall Time		-	76	-	ns	
E _{on}	Turn-On Energy		-	2.36	-	mJ	
E _{off}	Turn-Off Energy		-	1.17	-	mJ	
E _{total}	Total Switching Energy		-	3.54	-	mJ	
t _{rr}	Diode Reverse Recovery Time	T _J =25°C I _F =30A, di/dt=200A/μs, V _{CC} =400V	-	318	-	ns	
Q _{rr}	Diode Reverse Recovery Charge		-	0.8	-	μC	
I _{rm}	Diode Peak Reverse Recovery Current		-	6.0	-	A	
SWITCHING PARAMETERS, (Load Inductive, T_J=150°C)							
t _{D(on)}	Turn-On Delay Time	T _J =150°C V _{GE} =15V, V _{CC} =400V, I _C =60A, R _G =5Ω	-	33	-	ns	
t _r	Turn-On Rise Time		-	80	-	ns	
t _{D(off)}	Turn-Off Delay Time		-	195	-	ns	
t _f	Turn-Off Fall Time		-	75	-	ns	
E _{on}	Turn-On Energy		-	2.53	-	mJ	
E _{off}	Turn-Off Energy		-	1.51	-	mJ	
E _{total}	Total Switching Energy		-	4.04	-	mJ	
t _{rr}	Diode Reverse Recovery Time	T _J =150°C I _F =30A, di/dt=200A/μs, V _{CC} =400V	-	427	-	ns	
Q _{rr}	Diode Reverse Recovery Charge		-	1.6	-	μC	
I _{rm}	Diode Peak Reverse Recovery Current		-	7.5	-	A	

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

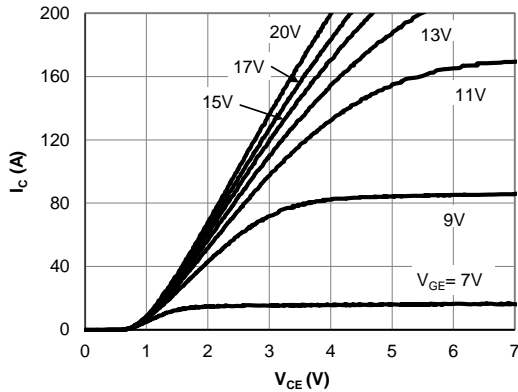


Figure 1: Output Characteristic
($T_j=25^\circ\text{C}$)

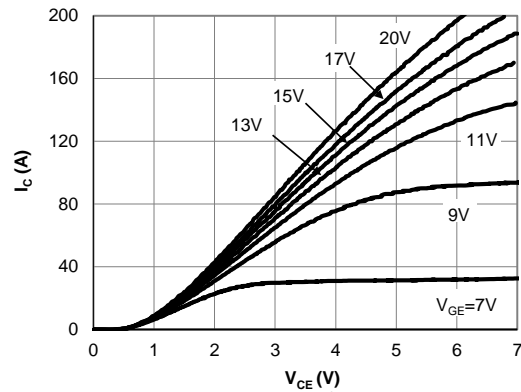


Figure 2: Output Characteristic
($T_j=150^\circ\text{C}$)

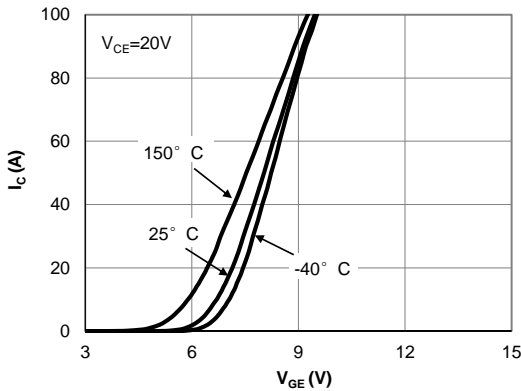


Figure 3: Transfer Characteristic

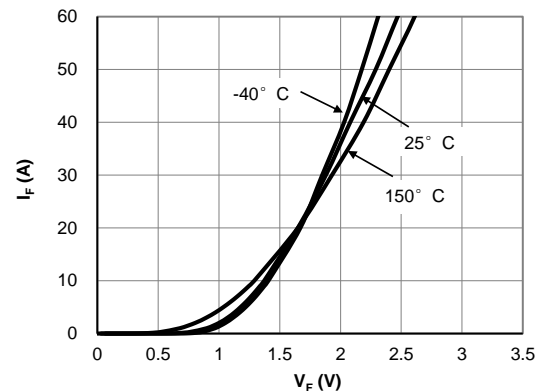


Figure 4: Diode Characteristic

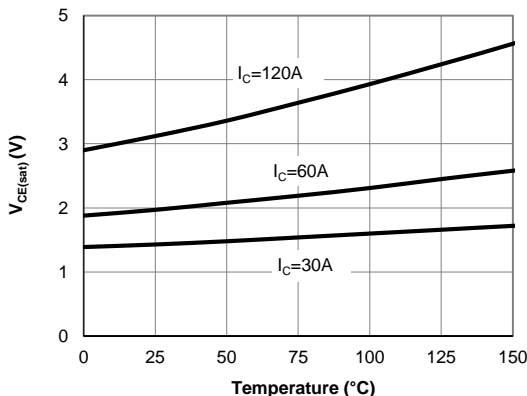


Figure 5: Collector-Emitter Saturation Voltage vs. Junction Temperature

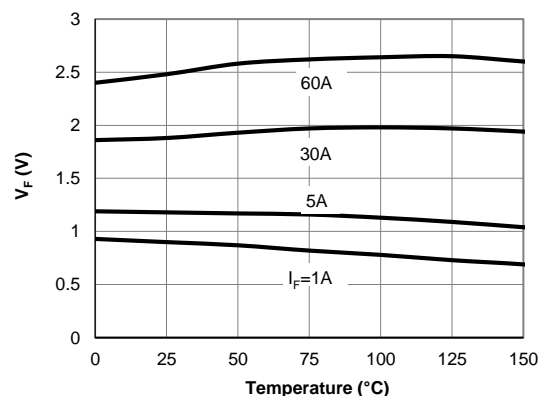


Figure 6: Diode Forward voltage vs. Junction Temperature

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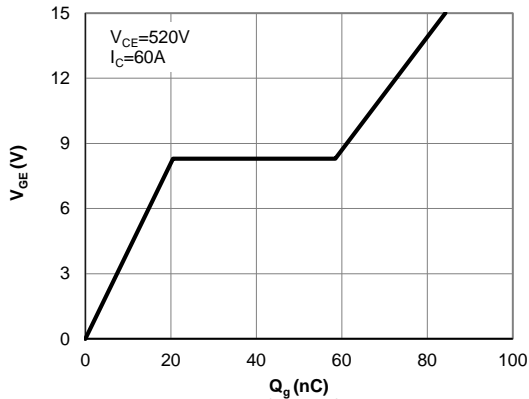


Figure 7: Gate-Charge Characteristics

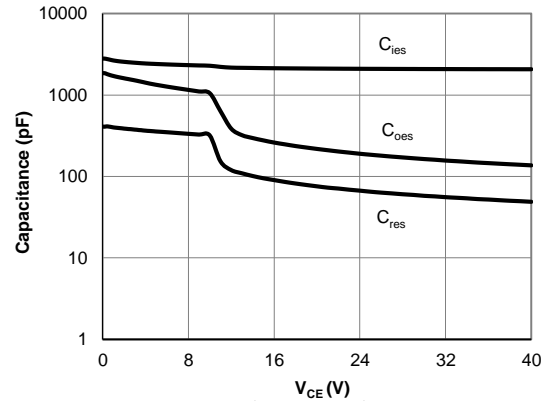


Figure 8: Capacitance Characteristic

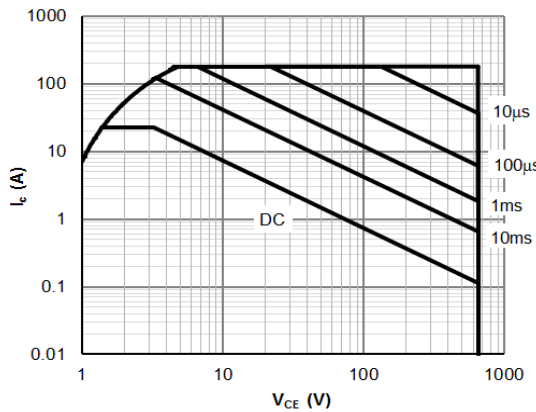


Figure 9: Forward Bias Safe Operating Area
($T_C=25^{\circ}\text{C}$, $V_{GE}=15\text{V}$)

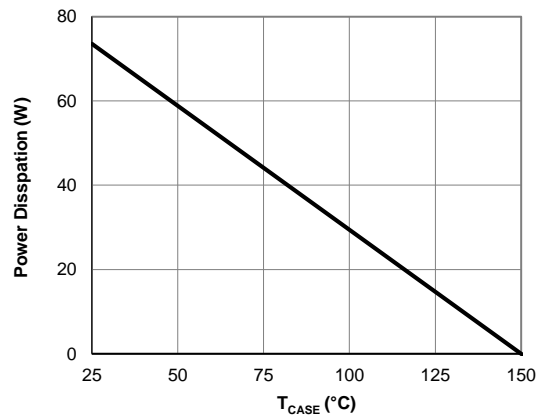


Figure 10: Power Dissipation as a Function of Case

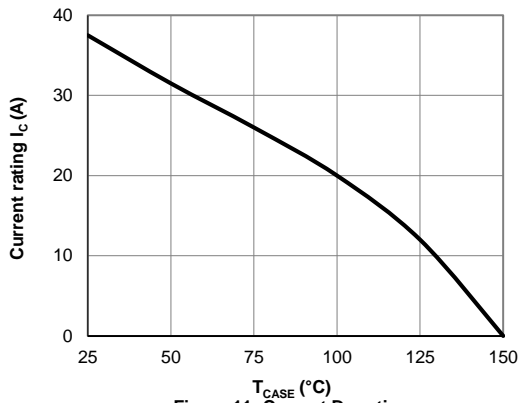


Figure 11: Current De-rating

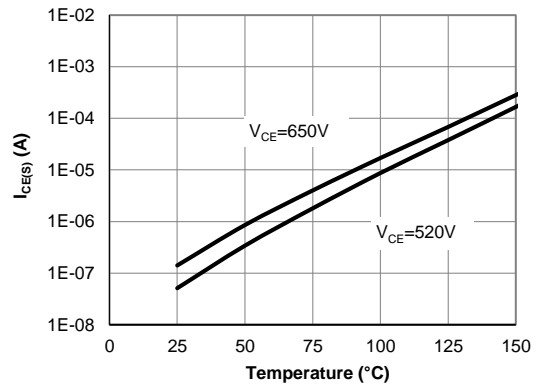


Figure 12: Diode Reverse Leakage Current vs. Junction Temperature

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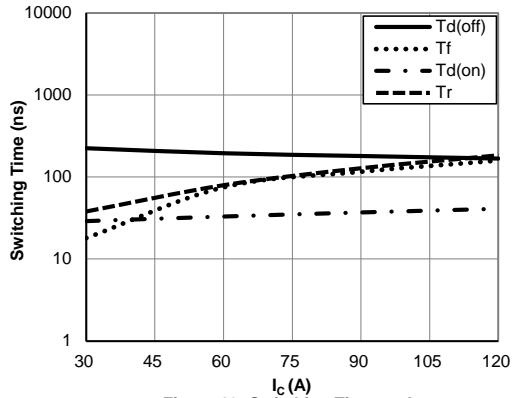


Figure 13: Switching Time vs. I_C
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=5\Omega$)

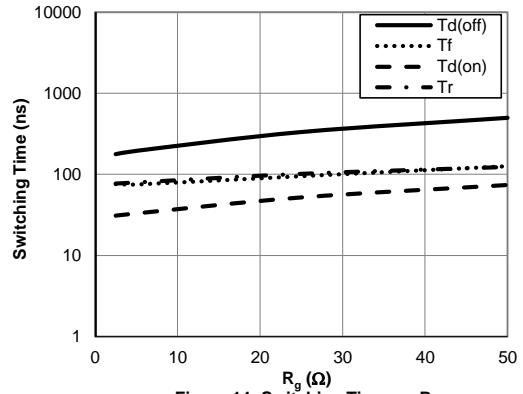


Figure 14: Switching Time vs. R_g
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=60\text{A}$)

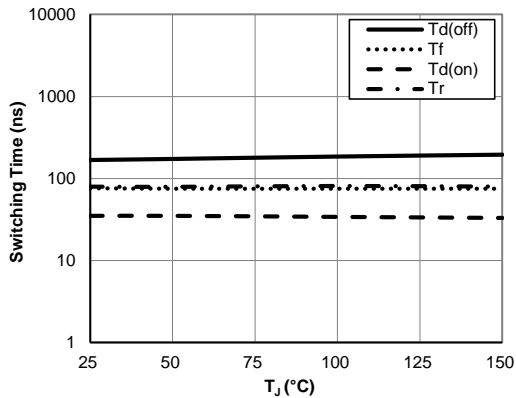


Figure 15: Switching Time vs. T_J
($V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=60\text{A}$, $R_g=5\Omega$)

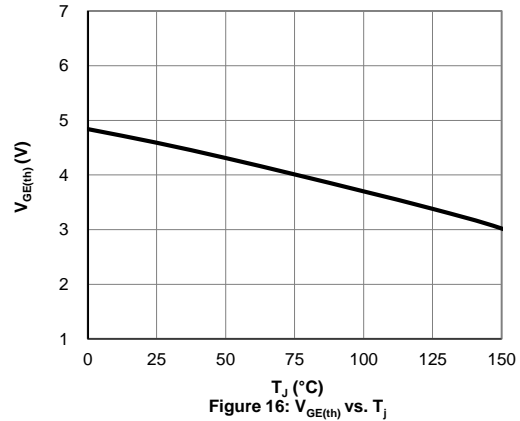


Figure 16: $V_{GE(th)}$ vs. T_J

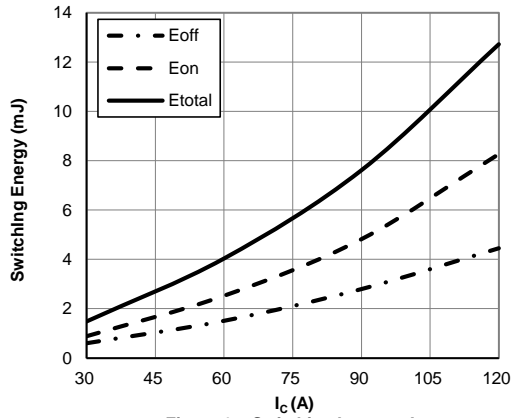


Figure 17: Switching Loss vs. I_C
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=5\Omega$)

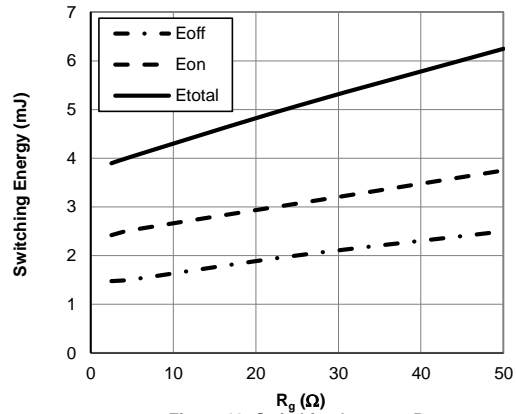


Figure 18: Switching Loss vs. R_g
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=60\text{A}$)

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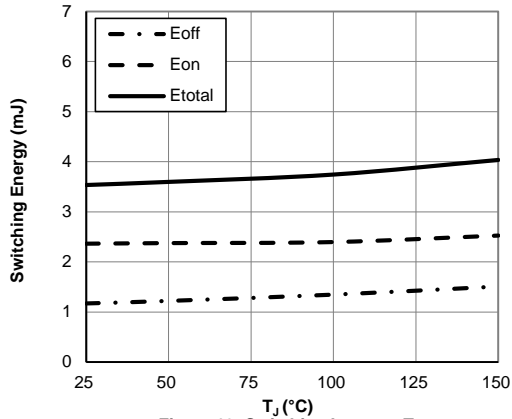


Figure 19: Switching Loss vs. T_j
($V_{GE}=15V, V_{CE}=400V, I_C=60A, R_g=5\Omega$)

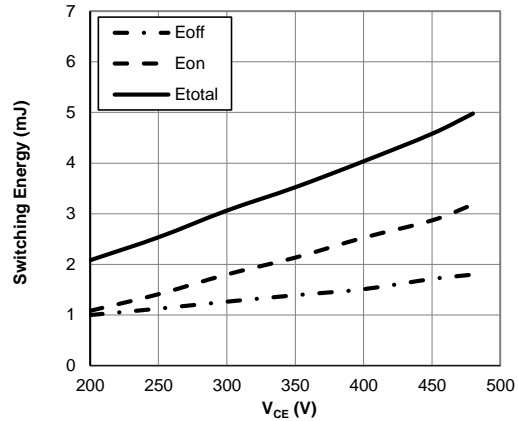


Figure 20: Switching Loss vs. V_{CE}
($T_j=150^\circ C, V_{GE}=15V, I_C=60A, R_g=5\Omega$)

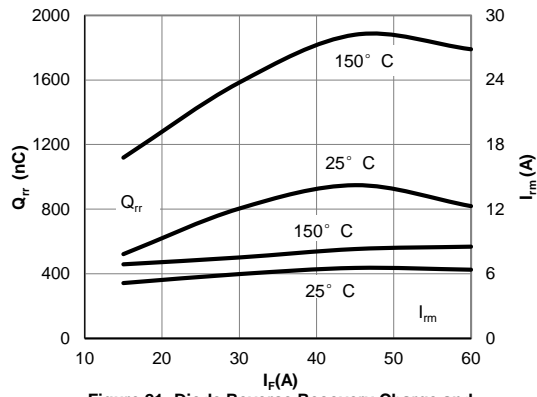


Figure 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

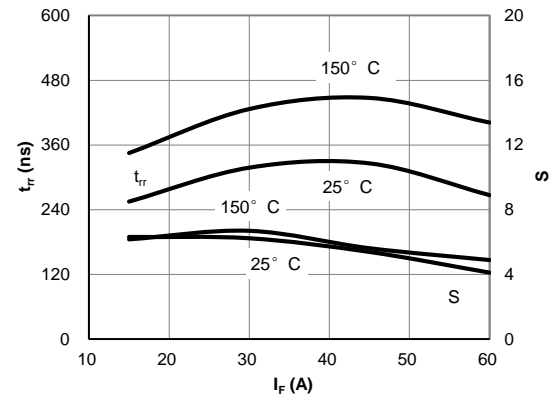


Figure 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

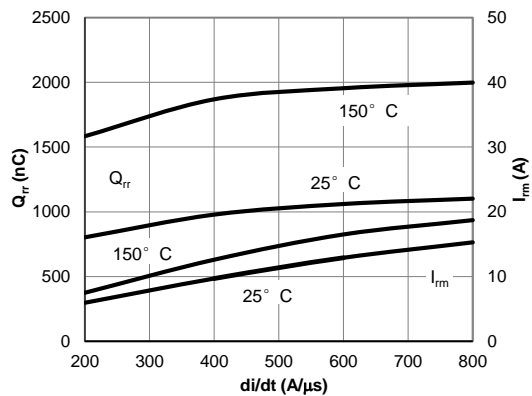


Figure 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=30A$)

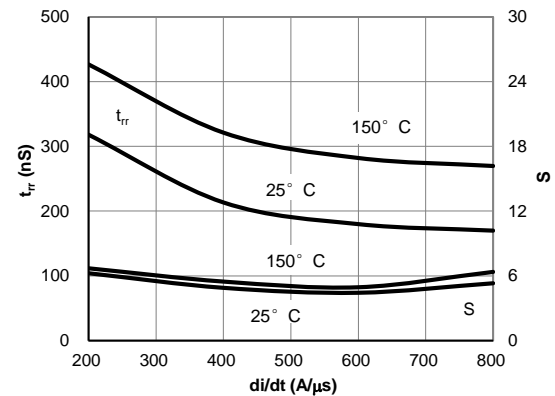


Figure 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=30A$)

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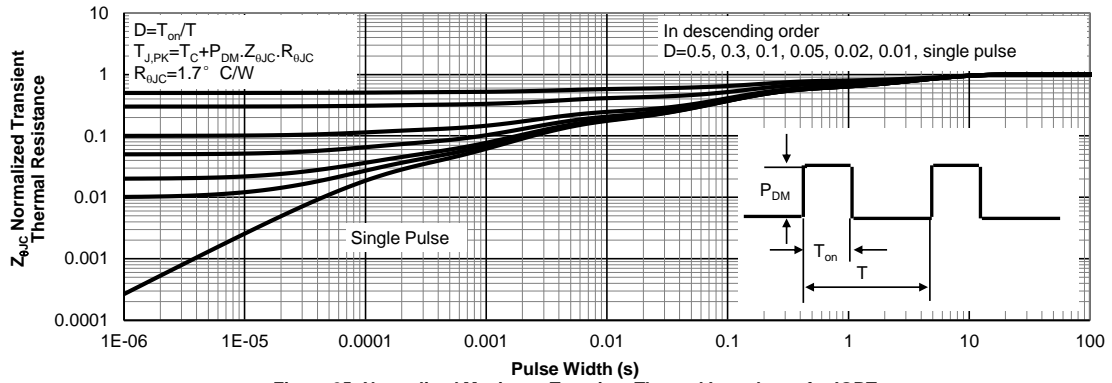


Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT

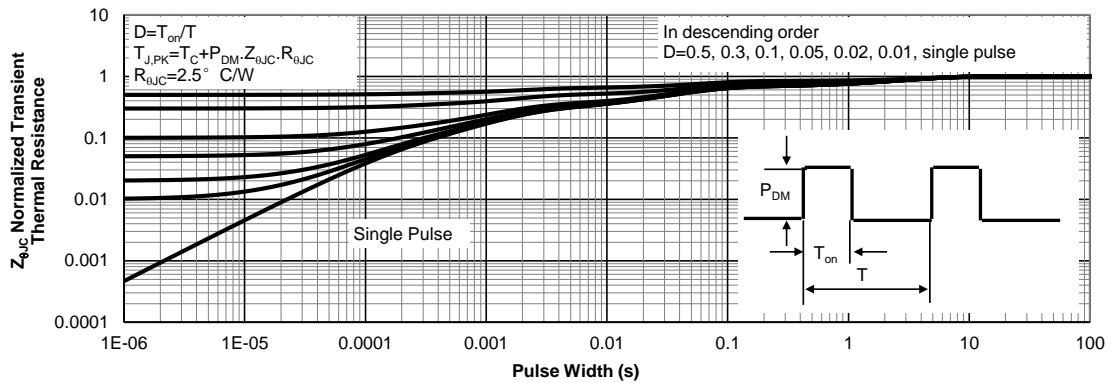


Figure 26: Normalized Maximum Transient Thermal Impedance for Diode

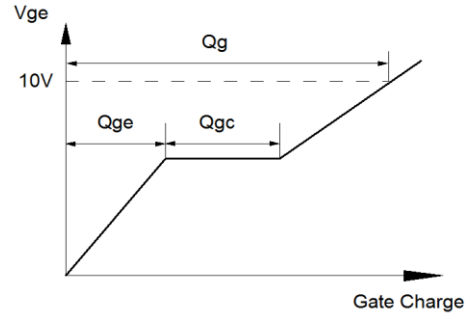
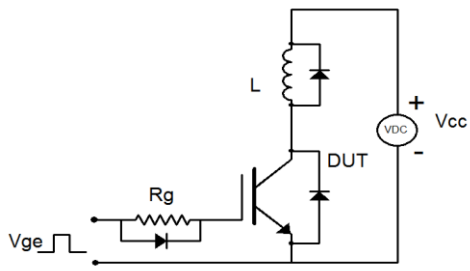


Figure A: Gate Charge Test Circuit & Waveforms

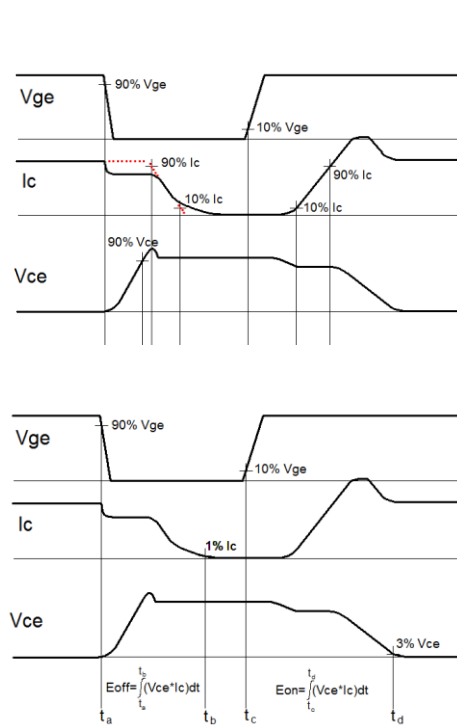
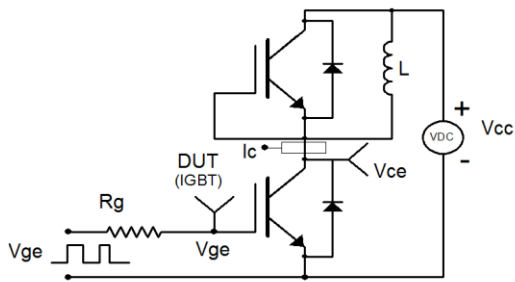


Figure B: Inductive Switching Test Circuit & Waveforms

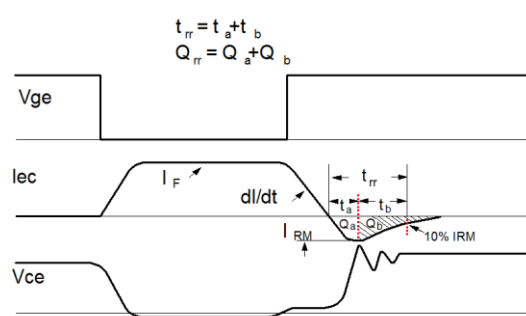
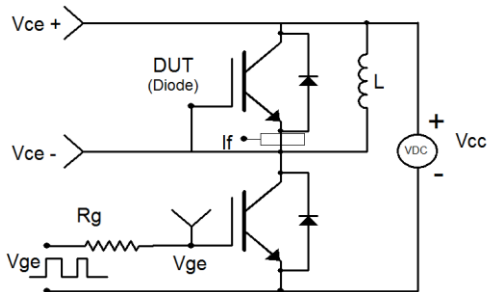


Figure C: Diode Recovery Test Circuit & Waveforms